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What is "Embedded - Microcontrollers"?

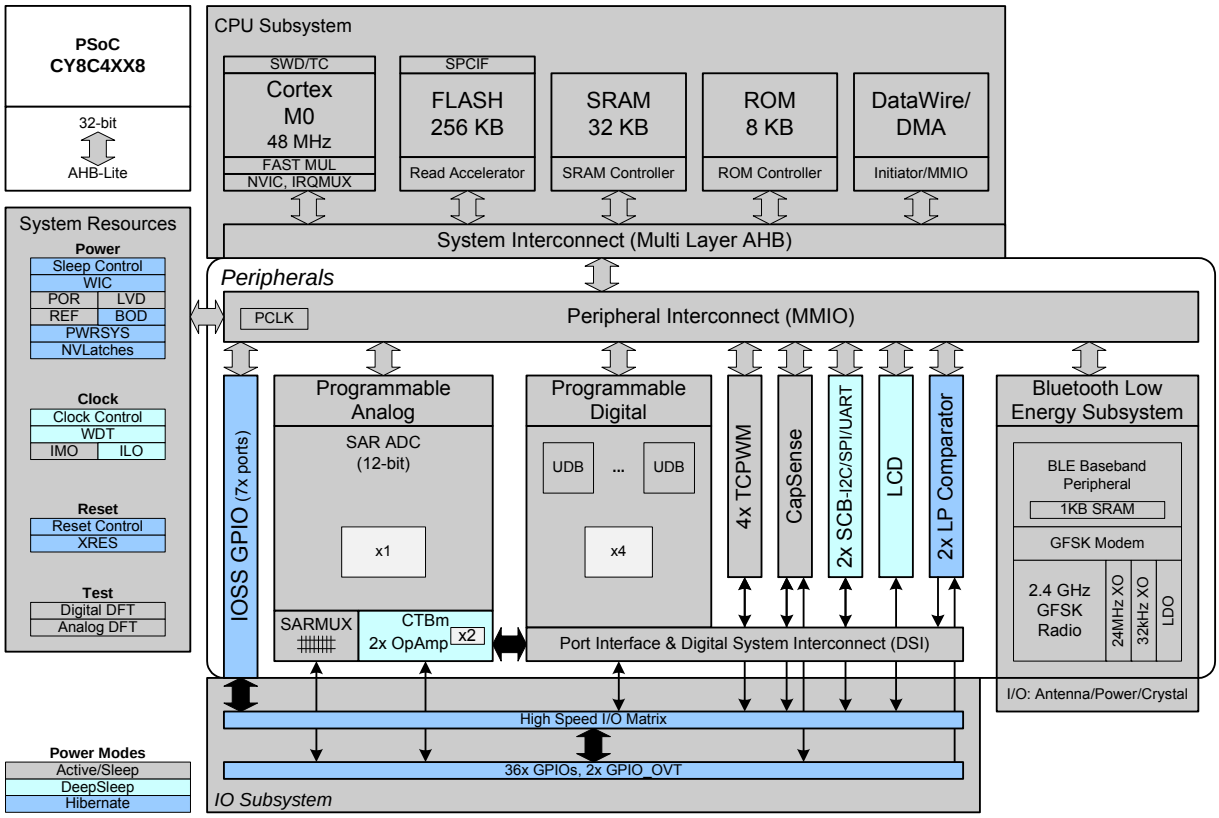
"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "Embedded - Microcontrollers"

Details	
Product Status	Active
Core Processor	ARM® Cortex®-M0
Core Size	32-Bit Single-Core
Speed	48MHz
Connectivity	I²C, IrDA, LINbus, Microwire, SmartCard, SPI, SSP, UART/USART
Peripherals	Bluetooth, Brown-out Detect/Reset, DMA LVD, POR, PWM, SmartCard, SmartSense, WDT
Number of I/O	36
Program Memory Size	256KB (256K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	32K x 8
Voltage - Supply (Vcc/Vdd)	1.71V ~ 5.5V
Data Converters	A/D 16x12b SAR; D/A 2xIDAC
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	56-UFQFN Exposed Pad
Supplier Device Package	56-QFN (7x7)
Purchase URL	https://www.e-xfl.com/product-detail/infineon-technologies/cy8c4248lqi-bl573

Contents

Figure 2. Block Diagram



The PSoC 4XX8 BLE 4.2 devices include extensive support for programming, testing, debugging, and tracing both hardware and firmware.

The ARM SWD interface supports all programming and debug features of the device.

Complete debug-on-chip functionality enables full-device debugging in the final system using the standard production device. It does not require special interfaces, debugging pods, simulators, or emulators. Only the standard programming connections are required to fully support debugging.

The PSoC Creator IDE provides fully integrated programming and debugging support for the PSoC 4XX8 BLE 4.2 devices. The SWD interface is fully compatible with industry-standard third-party tools. With the ability to disable debug features, very robust flash protection, and allowing customer-proprietary functionality to be implemented in on-chip programmable blocks, the PSoC 4XX8 BLE 4.2 family provides a level of security not possible with multi-chip application solutions or with microcontrollers.

Debug circuits are enabled by default and can only be disabled in firmware. If not enabled, the only way to re-enable them is to erase the entire device, clear flash protection, and reprogram the device with the new firmware that enables debugging.

Additionally, all device interfaces can be permanently disabled (device security) for applications concerned about phishing attacks due to a maliciously reprogrammed device or attempts to defeat security by starting and interrupting flash programming sequences. Because all programming, debug, and test interfaces are disabled when maximum device security is enabled, PSoC 4XX8 BLE 4.2 with device security enabled may not be returned for failure analysis. This is a trade-off the PSoC 4XX8 BLE 4.2 allows the customer to make.

Functional Definition

CPU and Memory Subsystem

CPU

The Cortex-M0 CPU in PSoC 4XX8 BLE 4.2 is part of the 32-bit MCU subsystem, which is optimized for low-power operation with extensive clock gating. It mostly uses 16-bit instructions and executes a subset of the Thumb-2 instruction set. This enables fully compatible binary upward migration of the code to higher-performance processors such as Cortex-M3 and M4. The Cypress implementation includes a hardware multiplier that provides a 32-bit result in one cycle. It includes a nested vectored interrupt controller (NVIC) block with 32 interrupt inputs and a wakeup interrupt controller (WIC). The WIC can wake the processor up from the Deep Sleep mode, allowing power to the main processor to be switched off when the chip is in the Deep Sleep mode. The Cortex-M0 CPU provides a nonmaskable interrupt (NMI) input, which is made available to the user when it is not in use for system functions requested by the user.

The CPU also includes an SWD interface, which is a 2-wire form of JTAG; the debug configuration used for PSoC 4XX8 BLE 4.2 has four break-point (address) comparators and two watchpoint (data) comparators.

Flash

The PSoC 4XX8 BLE 4.2 device has a flash module with either 128 KB or 256 KB of flash memory, tightly coupled to the CPU to improve average access times from the flash block. The flash block is designed to deliver 2 wait-state (WS) access time at 48 MHz and with 1-WS access time at 24 MHz. The flash accelerator delivers 85% of single-cycle SRAM access performance on average. Part of the flash module can be used to emulate EEPROM operation if required. Maximum erase and program time is 20 ms per row (256 bytes). This also applies to the emulated EEPROM.

SRAM

SRAM memory is retained during Hibernate.

SROM

The 8-KB supervisory ROM contains a library of executable functions for flash programming. These functions are accessed through supervisory calls (SVC) and enable in-system programming of the flash memory.

DMA

A DMA engine, with eight channels, is provided that can do 32-bit transfers and has chainable ping-pong descriptors.

System Resources

Power System

The power system is described in detail in the section Power on page 16. It provides an assurance that the voltage levels are as required for the respective modes, and can either delay the mode entry (on power-on reset (POR), for example) until voltage levels are as required or generate resets (brownout detect (BOD)) or interrupts when the power supply reaches a particular programmable level between 1.8 and 4.5 V (low voltage detect (LVD)).

PSoC 4XX8 BLE 4.2 operates with a single external supply (1.71 to 5.5 V without radio, and 1.9 V to 5.5 V with radio). The device has five different power modes; transitions between these modes are managed by the power system. PSoC 4XX8 BLE 4.2 provides Sleep, Deep Sleep, Hibernate, and Stop low-power modes. Refer to the *Technical Reference Manual* for more details.

Clock System

The PSoC 4XX8 BLE 4.2 clock system is responsible for providing clocks to all subsystems that require clocks and for switching between different clock sources without glitching. In addition, the clock system ensures that no metastable conditions occur.

The clock system for PSoC 4XX8 BLE 4.2 consists of the internal main oscillator (IMO), the internal low-speed oscillator (ILO), the 24-MHz external crystal oscillator (ECO) and the 32-kHz watch crystal oscillator (WCO). In addition, an external clock may be supplied from a pin.

IMO Clock Source

The IMO is the primary source of internal clocking in PSoC 4XX8 BLE 4.2. It is trimmed during testing to achieve the specified accuracy. Trim values are stored in nonvolatile latches (NVL). Additional trim settings from flash can be used to compensate for changes. The IMO default frequency is 24 MHz and it can be adjusted between 3 to 48 MHz in steps of 1 MHz. The IMO tolerance with Cypress-provided calibration settings is ±2%.

ILO Clock Source

The ILO is a very low-power oscillator, which is primarily used to generate clocks for the peripheral operation in the Deep Sleep mode. ILO-driven counters can be calibrated to the IMO to improve accuracy. Cypress provides a software component, which does the calibration.

External Crystal Oscillator (ECO)

The ECO is used as the active clock for the BLE subsystem to meet the ±50-ppm clock accuracy of the Bluetooth 4.2 Specification. PSoC 4XX8 BLE 4.2 includes a tunable load capacitor to tune the crystal clock frequency by measuring the actual clock frequency. The high-accuracy ECO clock can also be used as a system clock.

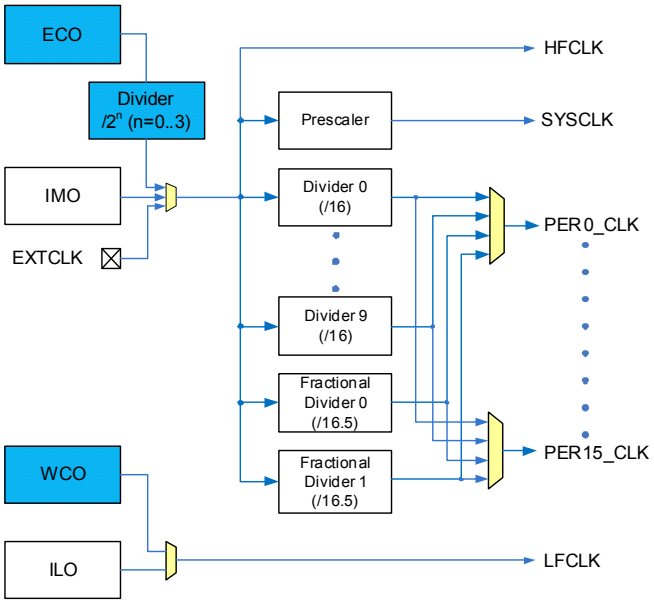
Watch Crystal Oscillator (WCO)

The WCO is used as the sleep clock for the BLE subsystem to meet the ±500-ppm clock accuracy for the Bluetooth 4.2 Specification. The sleep clock provides an accurate sleep timing and enables wakeup at the specified advertisement and connection intervals. The WCO output can be used to realize the real-time clock (RTC) function in firmware.

Watchdog Timer

A watchdog timer is implemented in the clock block running from the ILO or from the WCO; this allows the watchdog operation during Deep Sleep and generates a watchdog reset if not serviced before the timeout occurs. The watchdog reset is recorded in the Reset Cause register. With the WCO and firmware, an accurate real-time clock (within the bounds of the 32-kHz crystal accuracy) can be realized.

Figure 3. PSoC 4XX8 BLE 4.2 MCU Clocking Architecture



The HFCLK signal can be divided down (see Figure 3) to generate synchronous clocks for the UDBs, and the analog and digital peripherals. There are a total of 12 clock dividers for PSoC 4XX8 BLE 4.2: ten with 16-bit divide capability and two with 16.5-bit divide capability. This allows the generation of 16 divided clock signals, which can be used by peripheral blocks. The analog clock leads the digital clocks to allow analog events to occur before the digital clock-related noise is generated. The 16-bit and 16.5-bit dividers allow a lot of flexibility in generating fine-grained frequency values and are fully supported in PSoC Creator.

Reset

PSoC 4XX8 BLE 4.2 device can be reset from a variety of sources including a software reset. Reset events are asynchronous and guarantee reversion to a known state. The reset cause is recorded in a register, which is sticky through resets and allows the software to determine the cause of the reset. An XRES pin is reserved for an external reset to avoid complications with the configuration and multiple pin functions during power-on or reconfiguration. The XRES pin has an internal pull-up resistor that is always enabled.

Voltage Reference

The PSoC 4XX8 BLE 4.2 reference system generates all internally required references. A one-percent voltage reference spec is provided for the 12-bit ADC. To allow better signal-to-noise ratios (SNR) and better absolute accuracy, it is possible to bypass the internal reference using a GPIO pin or use an external reference for the SAR. Refer to Table 19, “SAR ADC AC Specifications,” on page 26 for details.

BLE Radio and Subsystem

PSoC 4XX8 BLE 4.2 incorporates a Bluetooth Smart subsystem that contains the Physical Layer (PHY) and Link Layer (LL) engines with an embedded AES-128 security engine. The physical layer consists of the digital PHY and the RF transceiver that transmits and receives GFSK packets at 1 Mbps over a 2.4-GHz ISM band, which is compliant with Bluetooth Smart Bluetooth Specification 4.2. The baseband controller is a composite hardware and firmware implementation that supports both master and slave modes. Key protocol elements, such as HCI and link control, are implemented in firmware. Time-critical functional blocks, such as encryption, CRC, data whitening, and access code correlation, are implemented in hardware (in the LL engine).

The RF transceiver contains an integrated balun, which provides a single-ended RF port pin to drive a 50-Ω antenna via a matching/filtering network. In the receive direction, this block converts the RF signal from the antenna to a digital bit stream after performing GFSK demodulation. In the transmit direction, this block performs GFSK modulation and then converts a digital baseband signal to a radio frequency before transmitting it to air through the antenna.

The Bluetooth Smart Radio and Subsystem (BLESS) requires a 1.9-V minimum supply (the range varies from 1.9 V to 5.5 V).

Key features of BLESS are as follows:

- Master and slave single-mode protocol stack with logical link control and adaptation protocol (L2CAP), attribute (ATT), and security manager (SM) protocols
- API access to generic attribute profile (GATT), generic access profile (GAP), and L2CAP
- L2CAP connection-oriented channel
- GAP features
  - Broadcaster, Observer, Peripheral, and Central roles
  - Security mode 1: Level 1, 2, 3, and 4
  - Security mode 2: Level 1 and 2
  - User-defined advertising data
  - Multiple bond support
- GATT features
  - GATT client and server
  - Supports GATT sub-procedures
  - 32-bit universally unique identifier (UUID)
- Security Manager (SM)
  - Pairing methods: Just works, Passkey Entry, Out of Band and Numeric Comparison
  - Authenticated man-in-the-middle (MITM) protection and data signing
  - LE Secure Connections (Bluetooth 4.2 feature)
- Link Layer (LL)
  - Master and Slave roles
  - 128-bit AES engine
  - Encryption
  - Low-duty cycle advertising
  - LE Ping
  - LE Data Packet Length Extension (Bluetooth 4.2 feature)
  - Link Layer Privacy (with extended scanning filter policy, Bluetooth 4.2 feature)
- Supports all SIG-adopted BLE profiles

Table 2. PSoC 4XX8 BLE 4.2 Pin List (WLCSP Package) *(continued)*

Pin	Name	Type	Description
G6	VSSR	GROUND	Radio ground
G7	VSSR	GROUND	Radio ground
G8	GANT	GROUND	Antenna shielding ground
G9	VSSR	GROUND	Radio ground
H1	NC	NC	Do not connect
H2	P0.5	GPIO	Port 0 Pin 5, analog/digital/lcd/csd
H3	P0.1	GPIO	Port 0 Pin 1, analog/digital/lcd/csd
H4	XTAL24O	CLOCK	24-MHz crystal
H5	XTAL24I	CLOCK	24-MHz crystal or external clock input
H6	VSSR	GROUND	Radio ground
H7	VSSR	GROUND	Radio ground
H8	ANT	ANTENNA	Antenna pin
J1	NC	NC	Do not connect
J2	P0.4	GPIO	Port 0 Pin 4, analog/digital/lcd/csd
J3	P0.0	GPIO	Port 0 Pin 0, analog/digital/lcd/csd
J4	VDDR	POWER	1.9-V to 5.5-V radio supply
J7	VDDR	POWER	1.9-V to 5.5-V radio supply
J8	NO CONNECT	–	–

High-speed I/O matrix (HSIOM) is a group of high-speed switches that routes GPIOs to the resources inside the device. These resources include CapSense, TCPWMs, I^2C, SPI, UART, and LCD. HSIOM_PORT_SELx are 32-bit-wide registers that control the routing of GPIOs. Each register controls one port; four dedicated bits are assigned to each GPIO in the port. This provides up to 16 different options for GPIO routing as shown in Table 3.

Table 3. HSIOM Port Settings

Value	Description
0	Firmware-controlled GPIO
1	Output is firmware-controlled, but Output Enable (OE) is controlled from DSI.
2	Both output and OE are controlled from DSI.
3	Output is controlled from DSI, but OE is firmware-controlled.
4	Pin is a CSD sense pin
5	Pin is a CSD shield pin
6	Pin is connected to AMUXA
7	Pin is connected to AMUXB
8	Pin-specific Active function #0
9	Pin-specific Active function #1
10	Pin-specific Active function #2

Table 3. HSIOM Port Settings *(continued)*

Value	Description
11	Reserved
12	Pin is an LCD common pin
13	Pin is an LCD segment pin
14	Pin-specific Deep-Sleep function #0
15	Pin-specific Deep-Sleep function #1

Electrical Specifications

Absolute Maximum Ratings

Table 5. Absolute Maximum Ratings[1]

Spec ID#	Parameter	Description	Min	Typ	Max	Units	Details/ Conditions
SID1	V_{DDD_ABS}	Analog, digital, or radio supply relative to V_{SS} (V_{SSD} = V_{SSA})	–0.5	–	6	V	Absolute max
SID2	V_{CCD_ABS}	Direct digital core voltage input relative to V_{SSD}	–0.5	–	1.95	V	Absolute max
SID3	V_{GPIO_ABS}	GPIO voltage	–0.5	–	V_{DD} +0.5	V	Absolute max
SID4	I_{GPIO_ABS}	Maximum current per GPIO	–25	–	25	mA	Absolute max
SID5	$I_{GPIO\_injection}$	GPIO injection current, Max for V_{IH} > V_{DDD}, and Min for V_{IL} < V_{SS}	–0.5	–	0.5	mA	Absolute max, current injected per pin
BID57	ESD_HBM	Electrostatic discharge human body model	2200	–	–	V	–
BID58	ESD_CDM	Electrostatic discharge charged device model	500	–	–	V	–
BID61	LU	Pin current for latch-up	–200	–	200	mA	–

Device-Level Specifications

All specifications are valid for –40 °C ≤ TA ≤ 85 °C and TJ ≤ 100 °C, except where noted. Specifications are valid for 1.71 V to 5.5 V, except where noted.

Table 6. DC Specifications

Spec ID#	Parameter	Description	Min	Typ	Max	Units	Details/ Conditions
SID6	V_{DD}	Power supply input voltage (V_{DDA} = V_{DDD} = V_{DD})	1.8	–	5.5	V	With regulator enabled
SID7	V_{DD}	Power supply input voltage unregulated (V_{DDA} = V_{DDD} = V_{DD})	1.71	1.8	1.89	V	Internally unregulated Supply
SID8	V_{DDR}	Radio supply voltage (Radio ON)	1.9	–	5.5	V	–
SID8A	V_{DDR}	Radio supply voltage (Radio OFF)	1.71	–	5.5	V	–
SID9	V_{CCD}	Digital regulator output voltage (for core logic)	–	1.8	–	V	–
SID10	C_{VCCD}	Digital regulator output bypass capacitor	1	1.3	1.6	µF	X5R ceramic or better
Active Mode, V_{DD} = 1.71 V to 5.5 V							–
SID13	I_{DD3}	Execute from flash; CPU at 3 MHz	–	2.1	–	mA	T = 25 °C, V_{DD} = 3.3 V
SID14	I_{DD4}	Execute from flash; CPU at 3 MHz	–	–	–	mA	T = –40 C to 85 °C
SID15	I_{DD5}	Execute from flash; CPU at 6 MHz	–	2.5	–	mA	T = 25 °C, V_{DD} = 3.3 V
SID16	I_{DD6}	Execute from flash; CPU at 6 MHz	–	–	–	mA	T = –40 °C to 85 °C
SID17	I_{DD7}	Execute from flash; CPU at 12 MHz	–	4	–	mA	T = 25 °C, V_{DD} = 3.3 V
SID18	I_{DD8}	Execute from flash; CPU at 12 MHz	–	–	–	mA	T = –40 °C to 85 °C

Note
1. Usage above the absolute maximum conditions listed in Table 5 may cause permanent damage to the device. Exposure to absolute maximum conditions for extended periods of time may affect device reliability. The maximum storage temperature is 150 °C in compliance with JEDEC Standard JESD22-A103, High Temperature Storage Life. When used below absolute maximum conditions but above normal operating conditions, the device may not operate to specification.

Table 6. DC Specifications *(continued)*

Spec ID#	Parameter	Description	Min	Typ	Max	Units	Details/ Conditions
SID19	I_{DD9}	Execute from flash; CPU at 24 MHz	–	7.1	–	mA	T = 25 °C, V_{DD} = 3.3 V
SID20	I_{DD10}	Execute from flash; CPU at 24 MHz	–	–	–	mA	T = –40 °C to 85 °C
SID21	I_{DD11}	Execute from flash; CPU at 48 MHz	–	13.4	–	mA	T = 25 °C, V_{DD} = 3.3 V
SID22	I_{DD12}	Execute from flash; CPU at 48 MHz	–	–	–	mA	T = –40 °C to 85 °C
Sleep Mode, V_{DD} = 1.8 to 5.5 V							
SID23	I_{DD13}	IMO on	–	–	–	mA	T = 25 °C, VDD = 3.3 V, SYSCLK = 3 MHz
Sleep Mode, V_{DD} and V_{DDR} = 1.9 to 5.5 V							
SID24	I_{DD14}	ECO on	–	–	–	mA	T = 25 °C, VDD = 3.3 V, SYSCLK = 3 MHz
Deep Sleep Mode, V_{DD} = 1.8 to 3.6 V							
SID25	I_{DD15}	WDT with WCO on	–	1.5	–	µA	T = 25 °C, V_{DD} = 3.3 V
SID26	I_{DD16}	WDT with WCO on	–	–	–	µA	T = –40 °C to 85 °C
Deep Sleep Mode, V_{DD} = 3.6 to 5.5 V							
SID27	I_{DD17}	WDT with WCO on	–	–	–	µA	T = 25 °C, V_{DD} = 5 V
SID28	I_{DD18}	WDT with WCO on	–	–	–	µA	T = –40 °C to 85 °C
Deep Sleep Mode, V_{DD} = 1.71 to 1.89 V (Regulator Bypassed)							
SID29	I_{DD19}	WDT with WCO on	–	–	–	µA	T = 25 °C
SID30	I_{DD20}	WDT with WCO on	–	–	–	µA	T = –40 °C to 85 °C
Deep Sleep Mode, V_{DD} = 1.8 to 3.6 V							
SID31	I_{DD21}	Opamp on	–	–	–	µA	T = 25 °C, V_{DD} = 3.3 V
SID32	I_{DD22}	Opamp on	–	–	–	µA	T = –40 °C to 85 °C
Deep Sleep Mode, V_{DD} = 3.6 to 5.5 V							
SID33	I_{DD23}	Opamp on	–	–	–	µA	T = 25 °C, V_{DD} = 5 V
SID34	I_{DD24}	Opamp on	–	–	–	µA	T = –40 °C to 85 °C
Deep Sleep Mode, V_{DD} = 1.71 to 1.89 V (Regulator Bypassed)							
SID35	I_{DD25}	Opamp on	–	–	–	µA	T = 25 °C
SID36	I_{DD26}	Opamp on	–	–	–	µA	T = –40 °C to 85 °C
Hibernate Mode, V_{DD} = 1.8 to 3.6 V							
SID37	I_{DD27}	GPIO and reset active	–	150	–	nA	T = 25 °C, V_{DD} = 3.3V
SID38	I_{DD28}	GPIO and reset active	–	–	–	nA	T = –40 °C to 85 °C
Hibernate Mode, V_{DD} = 3.6 to 5.5 V							
SID39	I_{DD29}	GPIO and reset active	–	–	–	nA	T = 25 °C, V_{DD} = 5 V
SID40	I_{DD30}	GPIO and reset active	–	–	–	nA	T = –40 °C to 85 °C
Hibernate Mode, V_{DD} = 1.71 to 1.89 V (Regulator Bypassed)							

Table 6. DC Specifications *(continued)*

Spec ID#	Parameter	Description	Min	Typ	Max	Units	Details/ Conditions
SID41	I_{DD31}	GPIO and reset active	–	–	–	nA	T = 25 °C
SID42	I_{DD32}	GPIO and reset active	–	–	–	nA	T = –40 °C to 85 °C
Stop Mode, V_{DD} = 1.8 to 3.6 V							
SID43	I_{DD33}	Stop mode current (V_{DD})	–	20	–	nA	T = 25 °C, V_{DD} = 3.3 V
SID44	I_{DD34}	Stop mode current (V_{DDR})	–	40	–-	nA	T = 25 °C, V_{DDR} = 3.3 V
SID45	I_{DD35}	Stop mode current (V_{DD})	–	–	–	nA	T = –40 °C to 85 °C
SID46	I_{DD36}	Stop mode current (V_{DDR})	–	–	–	nA	T = –40 °C to 85 °C, V_{DDR} = 1.9 V to 3.6 V
Stop Mode, V_{DD} = 3.6 to 5.5 V							
SID47	I_{DD37}	Stop mode current (V_{DD})	–	–	–	nA	T = 25 °C, V_{DD} = 5 V
SID48	I_{DD38}	Stop mode current (V_{DDR})	–	–	–	nA	T = 25 °C, V_{DDR} = 5 V
SID49	I_{DD39}	Stop mode current (V_{DD})	–	–	–	nA	T = –40 °C to 85 °C
SID50	I_{DD40}	Stop mode current (V_{DDR})	–	–	–	nA	T = –40 °C to 85 °C
Stop Mode, V_{DD} = 1.71 to 1.89 V (Regulator Bypassed)							
SID51	I_{DD41}	Stop mode current (V_{DD})	–	–	–	nA	T = 25 °C
SID52	I_{DD42}	Stop mode current (V_{DD})	–	–	–	nA	T = –40 °C to 85 °C

Table 7. AC Specifications

Spec ID#	Parameter	Description	Min	Typ	Max	Units	Details/ Conditions
SID53	F_{CPU}	CPU frequency	DC	–	48	MHz	1.71 V ≤ V_{DD} ≤ 5.5 V
SID54	T_{SLEEP}	Wakeup from Sleep mode	–	0	–	µs	Guaranteed by characterization
SID55	$T_{DEEPSLEEP}$	Wakeup from Deep Sleep mode	–	–	25	µs	24-MHz IMO. Guaranteed by characterization.
SID56	$T_{HIBERNATE}$	Wakeup from Hibernate mode	–	–	0.7	ms	Guaranteed by characterization
SID57	T_{STOP}	Wakeup from Stop mode	–	–	2.2	ms	Guaranteed by characterization

Table 9. GPIO AC Specifications *(continued)*

Spec ID#	Parameter	Description	Min	Typ	Max	Units	Details/ Conditions
SID83	$F_{GPIOUT2}$	GPIO Fout; 1.7 V≤ V_{DD} ≤ 3.3 V. Fast-Strong mode	–	–	16.7	MHz	90/10%, 25-pF load, 60/40 duty cycle
SID84	$F_{GPIOUT3}$	GPIO Fout; 3.3 V ≤ V_{DD} ≤ 5.5 V. Slow-Strong mode	–	–	7	MHz	90/10%, 25-pF load, 60/40 duty cycle
SID85	$F_{GPIOUT4}$	GPIO Fout; 1.7 V ≤ V_{DD} ≤ 3.3 V. Slow-Strong mode	–	–	3.5	MHz	90/10%, 25-pF load, 60/40 duty cycle
SID86	F_{GPIOIN}	GPIO input operating frequency; 1.71 V ≤ V_{DD} ≤ 5.5 V	–	–	48	MHz	90/10% V_{IO}

Table 10. OVT GPIO DC Specifications (P5_0 and P5_1 Only)

Spec ID#	Parameter	Description	Min	Typ	Max	Units	Details/ Conditions
SID71A	I_{IL}	Input leakage current (absolute value), V_{IH} > V_{DD}	–	–	10	µA	25 °C, V_{DD} = 0 V, V_{IH}= 3.0 V
SID66A	V_{OL}	Output voltage LOW level	–	–	0.4	V	I_{OL} = 20-mA, V_{DD} > 2.9-V

Table 11. OVT GPIO AC Specifications (P5_0 and P5_1 Only)

Spec ID#	Parameter	Description	Min	Typ	Max	Units	Details/ Conditions
SID78A	T_{RISE_OVFS}	Output rise time in Fast-Strong mode	1.5	–	12	ns	25-pF load, 10%–90%, V_{DD}=3.3-V
SID79A	T_{FALL_OVFS}	Output fall time in Fast-Strong mode	1.5	–	12	ns	25-pF load, 10%–90%, V_{DD}=3.3-V
SID80A	T_{RISSS}	Output rise time in Slow-Strong mode	10	–	60	ns	25-pF load, 10%–90%, V_{DD}=3.3-V
SID81A	T_{FALLSS}	Output fall time in Slow-Strong mode	10	–	60	ns	25-pF load, 10%–90%, V_{DD}=3.3-V
SID82A	$F_{GPIOUT1}$	GPIO F_{OUT}; 3.3 V ≤ V_{DD} ≤ 5.5 V Fast-Strong mode	–	–	24	MHz	90/10%, 25-pF load, 60/40 duty cycle
SID83A	$F_{GPIOUT2}$	GPIO F_{OUT}; 1.71 V ≤ V_{DD} ≤ 3.3 V Fast-Strong mode	–	–	16	MHz	90/10%, 25-pF load, 60/40 duty cycle

XRES

Table 12. XRES DC Specifications

Spec ID#	Parameter	Description	Min	Typ	Max	Units	Details/ Conditions
SID87	V_{IH}	Input voltage HIGH threshold	0.7 × V_{DDD}	–	–	V	CMOS input
SID88	V_{IL}	Input voltage LOW threshold	–	–	0.3 × V_{DDD}	V	CMOS input
SID89	Rpullup	Pull-up resistor	3.5	5.6	8.5	kΩ	–
SID90	C_{IN}	Input capacitance	–	3	–	pF	–
SID91	$V_{HYSXRES}$	Input voltage hysteresis	–	100	–	mV	–
SID92	I_{DIODE}	Current through protection diode to V_{DDD}/V_{SS}	–	–	100	µA	–

Table 14. Opamp Specifications *(continued)*

Spec ID#	Parameter	Description	Min	Typ	Max	Units	Details/ Conditions
SID122	V_{N3}	Input referred, 10-kHz, power = high	–	28	–	nV/rtHz	–
SID123	V_{N4}	Input referred, 100-kHz, power = high	–	15	–	nV/rtHz	–
SID124	C_{LOAD}	Stable up to maximum load. Performance specs at 50 pF	–	–	125	pF	–
SID125	Slew_rate	Cload = 50 pF, Power = High, $V_{DDA} \geq 2.7$ V	6	–	–	V/µsec	–
SID126	T_op_wake	From disable to enable, no external RC dominating	–	300	–	µsec	–
Comp_mode (Comparator Mode; 50-mV Drive, $T_{RISE} = T_{FALL}$ (Approx.)							
SID127	T_{PD1}	Response time; power = high	–	150	–	nsec	–
SID128	T_{PD2}	Response time; power = medium	–	400	–	nsec	–
SID129	T_{PD3}	Response time; power = low	–	2000	–	nsec	–
SID130	Vhyst_op	Hysteresis	–	10	–	mV	–
Deep Sleep (Deep Sleep mode operation is only guaranteed for $V_{DDA} > 2.5$ V)							
SID131	GBW_DS	Gain bandwidth product	–	50	–	kHz	–
SID132	IDD_DS	Current	–	15	–	µA	–
SID133	Vos_DS	Offset voltage	–	5	–	mV	–
SID134	Vos_dr_DS	Offset voltage drift	–	20	–	µV/°C	–
SID135	Vout_DS	Output voltage	0.2	–	V_{DD}–0.2	V	–
SID136	Vcm_DS	Common mode voltage	0.2	–	V_{DD}–1.8	V	–

Table 15. Comparator DC Specifications[3]

Spec ID#	Parameter	Description	Min	Typ	Max	Units	Details/ Conditions
SID140	$V_{OFFSET1}$	Input offset voltage, Factory trim	–	–	±10	mV	–
SID141	$V_{OFFSET2}$	Input offset voltage, Custom trim	–	–	±6	mV	–
SID141A	$V_{OFFSET3}$	Input offset voltage, ultra-low-power mode	–	±12	–	mV	$V_{DDD} \geq 2.6$ V for Temp < 0°C, $V_{DDD} \geq 1.8$ V for Temp > 0 °C
SID142	V_{HYST}	Hysteresis when enabled. Common Mode voltage range from 0 to VDD –1	–	10	35	mV	–
SID143	V_{ICM1}	Input common mode voltage in normal mode	0	–	V_{DDD} –0.1	V	Modes 1 and 2
SID144	V_{ICM2}	Input common mode voltage in low power mode	0	–	V_{DDD}	V	–
SID145	V_{ICM3}	Input common mode voltage in ultra low power mode	0	–	V_{DDD} –1.15	V	$V_{DDD} \geq 2.6$ V for Temp < 0°C, $V_{DDD} \geq 1.8$ V for Temp > 0 °C
SID146	CMRR	Common mode rejection ratio	50	–	–	dB	$V_{DDD} \geq 2.7$ V
SID147	CMRR	Common mode rejection ratio	42	–	–	dB	$V_{DDD} \leq 2.7$ V
SID148	I_{CMP1}	Block current, normal mode	–	–	400	µA	–
SID149	I_{CMP2}	Block current, low power mode	–	–	100	µA	–

Note
3. ULP LCOMP operating conditions:
   - V_{DDD} 2.6 V-5.5 V for datasheet temp range < 0 °C
   - V_{DDD} 1.8 V-5.5 V for datasheet temp range ≥ 0 °C

Table 15. Comparator DC Specifications[3] *(continued)*

Spec ID#	Parameter	Description	Min	Typ	Max	Units	Details/ Conditions
SID150	I_{CMP3}	Block current in ultra low-power mode	–	6	–	µA	V_{DDD} ≥ 2.6 V for Temp < 0°C, V_{DDD} ≥ 1.8 V for Temp > 0 °C
SID151	Z_{CMP}	DC input impedance of comparator	35	–	–	MΩ	–

Table 16. Comparator AC Specifications[4]

Spec ID#	Parameter	Description	Min	Typ	Max	Units	Details/ Conditions
SID152	T_{RESP1}	Response time, normal mode, 50-mV overdrive	–	38	–	ns	50-mV overdrive
SID153	T_{RESP2}	Response time, low power mode, 50-mV overdrive	–	70	–	ns	50-mV overdrive
SID154	T_{RESP3}	Response time, ultra-low-power mode, 50-mV overdrive	–	2.3	–	µs	200-mV overdrive. V_{DDD} ≥ 2.6 V for Temp < 0°C, V_{DDD} ≥ 1.8 V for Temp > 0 °C

Temperature Sensor

Table 17. Temperature Sensor Specifications

Spec ID#	Parameter	Description	Min	Typ	Max	Units	Details/Conditions
SID155	$T_{SENSACC}$	Temperature sensor accuracy	–5	±1	5	°C	–40 to +85 °C

SAR ADC

Table 18. SAR ADC DC Specifications

Spec ID#	Parameter	Description	Min	Typ	Max	Units	Details/Conditions
SID156	A_RES	Resolution	–	–	12	bits	–
SID157	A_CHNIS_S	Number of channels - single-ended	–	–	8	–	8 full-speed
SID158	A-CHNKS_D	Number of channels - differential	–	–	4	–	Diff inputs use neighboring I/O
SID159	A-MONO	Monotonicity	–	–	–	–	Yes
SID160	A_GAINERR	Gain error	–	–	±0.1	%	With external reference.
SID161	A_OFFSET	Input offset voltage	–	–	2	mV	Measured with 1-V V_{REF}
SID162	A_ISAR	Current consumption	–	–	1	mA	–
SID163	A_VINS	Input voltage range - single-ended	V_{SS}	–	V_{DDA}	V	–
SID164	A_VIND	Input voltage range - differential	V_{SS}	–	V_{DDA}	V	–
SID165	A_INRES	Input resistance	–	–	2.2	kΩ	–
SID166	A_INCAP	Input capacitance	–	–	10	pF	–
SID312	VREFSAR	Trimmed internal reference to SAR	–1	–	1	%	Percentage of Vbg (1.024-V)

Note
4. ULP LCOMP operating conditions:
   - V_{DDD} 2.6 V-5.5 V for datasheet temp range < 0 °C
   - V_{DDD} 1.8 V-5.5 V for datasheet temp range ≥ 0 °C

Table 19. SAR ADC AC Specifications

Spec ID#	Parameter	Description	Min	Typ	Max	Units	Details/ Conditions
SID167	A_psrr	Power supply rejection ratio	70	–	–	dB	Measured at 1-V reference
SID168	A_cmrr	Common mode rejection ratio	66	–	–	dB	–
SID169	A_samp	Sample rate	–	–	1	Msps	806 Ksps for PSoC 41X8_BLE devices
SID313	Fsarintref	SAR operating speed without external ref. bypass	–	–	100	Ksps	12-bit resolution
SID170	A_snr	Signal-to-noise ratio (SNR)	65	–	–	dB	Fin = 10 kHz
SID171	A_bw	Input bandwidth without aliasing	–	–	A_samp/2	kHz	–
SID172	A_inl	Integral non linearity. V_{DD} = 1.71 to 5.5 V, 1 Msps	–1.7	–	2	LSB	Vref = 1 V to V_{DD}
SID173	A_INL	Integral non linearity. V_{DDD} = 1.71 to 3.6 V, 1 Msps	–1.5	–	1.7	LSB	Vref = 1.71 V to V_{DD}
SID174	A_INL	Integral non linearity. V_{DD} = 1.71 to 5.5 V, 500 Ksps	–1.5	–	1.7	LSB	Vref = 1 V to V_{DD}
SID175	A_dnl	Differential non linearity. V_{DD} = 1.71 to 5.5 V, 1 Msps	–1	–	2.2	LSB	Vref = 1 V to V_{DD}
SID176	A_DNL	Differential non linearity. V_{DD} = 1.71 to 3.6 V, 1 Msps	–1	–	2	LSB	Vref = 1.71 V to V_{DD}
SID177	A_DNL	Differential non linearity. V_{DD} = 1.71 to 5.5 V, 500 Ksps	–1	–	2.2	LSB	Vref = 1 V to V_{DD}
SID178	A_thd	Total harmonic distortion	–	–	–65	dB	Fin = 10 kHz

CSD

Table 20. CSD Block Specifications

Spec ID#	Parameter	Description	Min	Typ	Max	Units	Details/ Conditions
SID179	V_{CSD}	Voltage range of operation	1.71	–	5.5	V	–
SID180	IDAC1	DNL for 8-bit resolution	–1	–	1	LSB	–
SID181	IDAC1	INL for 8-bit resolution	–3	–	3	LSB	–
SID182	IDAC2	DNL for 7-bit resolution	–1	–	1	LSB	–
SID183	IDAC2	INL for 7-bit resolution	–3	–	3	LSB	–
SID184	SNR	Ratio of counts of finger to noise	5	–	–	Ratio	Capacitance range of 9 to 35 pF, 0.1 pF sensitivity. Radio is not operating during the scan
SID185	I_{DAC1_CRT1}	Output current of IDAC1 (8 bits) in High range	–	612	–	µA	–
SID186	I_{DAC1_CRT2}	Output current of IDAC1 (8 bits) in Low range	–	306	–	µA	–
SID187	I_{DAC2_CRT1}	Output current of IDAC2 (7 bits) in High range	–	305	–	µA	–
SID188	I_{DAC2_CRT2}	Output current of IDAC2 (7 bits) in Low range	–	153	–	µA	–

Table 38. Flash AC Specifications

Spec ID	Parameter	Description	Min	Typ	Max	Units	Details/Conditions
SID250	$T_{ROWWRITE}$[5]	Row (block) write time (erase and program)	–	–	20	ms	Row (block) = 256 bytes
SID251	$T_{ROWERASE}$[5]	Row erase time	–	–	13	ms	–
SID252	$T_{ROWPROGRAM}$[5]	Row program time after erase	–	–	7	ms	–
SID253	$T_{BULKERASE}$[5]	Bulk erase time (256 KB)	–	–	35	ms	–
SID254	$T_{DEVPROG}$[5]	Total device program time	–	–	50	seconds	For 256 KB
SID255	F_{END}	Flash endurance	100 K	–	–	cycles	–
SID256	F_{RET}	Flash retention. $T_A \leq 55$ °C, 100 K P/E cycles	20	–	–	years	–
SID257	F_{RET2}	Flash retention. $T_A \leq 85$ °C, 10 K P/E cycles	10	–	–	years	–

System Resources

Power-on-Reset (POR)

Table 39. POR DC Specifications

Spec ID	Parameter	Description	Min	Typ	Max	Units	Details/Conditions
SID258	$V_{RISEIPOR}$	Rising trip voltage	0.80	–	1.45	V	–
SID259	$V_{FALLIPOR}$	Falling trip voltage	0.75	–	1.40	V	–
SID260	$V_{IPORHYST}$	Hysteresis	15	–	200	mV	–

Table 40. POR AC Specifications

Spec ID	Parameter	Description	Min	Typ	Max	Units	Details/Conditions
SID264	T_{PPOR_TR}	PPOR response time in Active and Sleep modes	–	–	1	µs	–

Table 41. Brown-Out Detect

Spec ID#	Parameter	Description	Min	Typ	Max	Units	Details/ Conditions
SID261	$V_{FALLPPOR}$	BOD trip voltage in Active and Sleep modes	1.64	–	–	V	–
SID262	$V_{FALLDPSLP}$	BOD trip voltage in Deep Sleep mode	1.4	–	–	V	–

Table 42. Hibernate Reset

Spec ID#	Parameter	Description	Min	Typ	Max	Units	Details/ Conditions
SID263	$V_{HBRTRIP}$	BOD trip voltage in Hibernate mode	1.1	–	–	V	–

Note

5. It can take as much as 20 milliseconds to write to flash. During this time, the device should not be reset, or flash operations will be interrupted and cannot be relied on to have completed. Reset sources include the XRES pin, software resets, CPU lockup states and privilege violations, improper power supply levels, and watchdogs. Make certain that these are not inadvertently activated.

Table 52. BLE Subsystem *(continued)*

Spec ID#	Parameter	Description	Min	Typ	Max	Units	Details/ Conditions
SID356	RXSE2	Receiver spurious emission 1.0 GHz to 12.75 GHz	–	–	–47	dBm	1-MHz measurement bandwidth ETSI EN300 328 V1.8.1
RF Transmitter Specifications							
SID357	TXP, ACC	RF power accuracy	–	±4	–	dB	–
SID358	TXP, RANGE	RF power control range	–	20	–	dB	–
SID359	TXP, 0dBm	Output power, 0-dB Gain setting (PA7)	–	0	–	dBm	–
SID360	TXP, MAX	Output power, maximum power setting (PA10)	–	3	–	dBm	–
SID361	TXP, MIN	Output power, minimum power setting (PA1)	–	–18	–	dBm	–
SID362	F2AVG	Average frequency deviation for 10101010 pattern	185	–	–	kHz	RF-PHY Specification (TRM-LE/CA/05/C)
SID363	F1AVG	Average frequency deviation for 11110000 pattern	225	250	275	kHz	RF-PHY Specification (TRM-LE/CA/05/C)
SID364	EO	Eye opening = ΔF2AVG/ΔF1AVG	0.8	–	–		RF-PHY Specification (TRM-LE/CA/05/C)
SID365	FTX, ACC	Frequency accuracy	–150	–	150	kHz	RF-PHY Specification (TRM-LE/CA/06/C)
SID366	FTX, MAXDR	Maximum frequency drift	–50	–	50	kHz	RF-PHY Specification (TRM-LE/CA/06/C)
SID367	FTX, INITDR	Initial frequency drift	–20	–	20	kHz	RF-PHY Specification (TRM-LE/CA/06/C)
SID368	FTX, DR	Maximum drift rate	–20	–	20	kHz/ 50 µs	RF-PHY Specification (TRM-LE/CA/06/C)
SID369	IBSE1	In-band spurious emission at 2-MHz offset	–	–	–20	dBm	RF-PHY Specification (TRM-LE/CA/03/C)
SID370	IBSE2	In-band spurious emission at ≥3-MHz offset	–	–	-30	dBm	RF-PHY Specification (TRM-LE/CA/03/C)
SID371	TXSE1	Transmitter spurious emissions (average), <1.0 GHz	–	–	-55.5	dBm	FCC-15.247
SID372	TXSE2	Transmitter spurious emissions (average), >1.0 GHz	–	–	-41.5	dBm	FCC-15.247
RF Current Specifications							
SID373	IRX	Receive current in normal mode	–	18.7	–	mA	–
SID373A	IRX_RF	Radio receive current in normal mode	–	16.4	–	mA	Measured at V_{DDR}
SID374	IRX, HIGHGAIN	Receive current in high-gain mode	–	21.5	–	mA	–
SID375	ITX, 3dBm	TX current at 3-dBm setting (PA10)	–	20	–	mA	–
SID376	ITX, 0dBm	TX current at 0-dBm setting (PA7)	–	16.5	–	mA	–
SID376A	ITX_RF, 0dBm	Radio TX current at 0 dBm setting (PA7)	–	15.6	–	mA	Measured at V_{DDR}
SID376B	ITX_RF, 0dBm	Radio TX current at 0 dBm excluding Balun loss	–	14.2	–	mA	Guaranteed by design simulation
SID377	ITX,-3dBm	TX current at –3-dBm setting (PA4)	–	15.5	–	mA	–

Table 52. BLE Subsystem *(continued)*

Spec ID#	Parameter	Description	Min	Typ	Max	Units	Details/ Conditions
SID378	ITX,-6dBm	TX current at –6-dBm setting (PA3)	–	14.5	–	mA	–
SID379	ITX,-12dBm	TX current at –12-dBm setting (PA2)	–	13.2	–	mA	–
SID380	ITX,-18dBm	TX current at –18-dBm setting (PA1)	–	12.5	–	mA	–
SID380A	Iavg_1sec, 0dBm	Average current at 1-second BLE connection interval	–	17.1	–	µA	TXP: 0 dBm; ±20-ppm master and slave clock accuracy.
SID380B	Iavg_4sec, 0dBm	Average current at 4-second BLE connection interval	–	6.1	–	µA	TXP: 0 dBm; ±20-ppm master and slave clock accuracy.
General RF Specifications							
SID381	FREQ	RF operating frequency	2400	–	2482	MHz	–
SID382	CHBW	Channel spacing	–	2	–	MHz	–
SID383	DR	On-air data rate	–	1000	–	kbps	–
SID384	IDLE2TX	BLE.IDLE to BLE. TX transition time	–	120	140	µs	–
SID385	IDLE2RX	BLE.IDLE to BLE. RX transition time	–	75	120	µs	–
RSSI Specifications							
SID386	RSSI, ACC	RSSI accuracy	–	±5	–	dB	–
SID387	RSSI, RES	RSSI resolution	–	1	–	dB	–
SID388	RSSI, PER	RSSI sample period	–	6	–	µs	–

Table 53. ECO Specifications

Spec ID#	Parameter	Description	Min	Typ	Max	Units	Details/ Conditions
SID389	F_{ECO}	Crystal frequency	–	24	–	MHz	–
SID390	F_{TOL}	Frequency tolerance	–50	–	50	ppm	–
SID391	ESR	Equivalent series resistance	–	–	60	Ω	–
SID392	PD	Drive level	–	–	100	µW	–
SID393	T_{START1}	Startup time (Fast Charge on)	–	–	850	µs	–
SID394	T_{START2}	Startup time (Fast Charge off)	–	–	3	ms	–
SID395	C_L	Load capacitance	–	8	–	pF	–
SID396	C0	Shunt capacitance	–	1.1	–	pF	–
SID397	I_{ECO}	Operating current	–	1400	–	µA	–

Ordering Code Definitions

Example

CY8 C

4 : PSoC 4

2 : 4200 Family

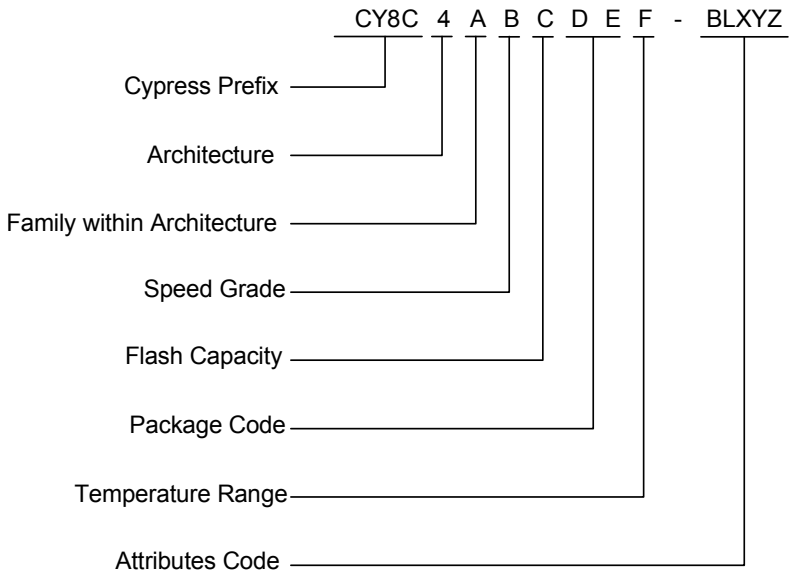
4 : 48 MHz

8 : 256 KB

LQ : QFN

I : Industrial

BLXYZ: Attributes



The Field Values are listed in the following table:

Field	Description	Values	Meaning
CY8C	Cypress Prefix		
4	Architecture	4	PSoC 4
A	Family within architecture	1	4100-BLE Family
		2	4200-BLE Family
B	CPU Speed	2	24 MHz
		4	48 MHz
C	Flash Capacity	8, 7	256, 128 KB
DE	Package Code	FN	WLCSP
		LQ	QFN
		FL	Thin CSP
F	Temperature Range	I	Industrial
BLXYZ	Attributes Code	BL500-BL599	BL5 indicates Bluetooth LE 4.2 support

Packaging

Table 56. Package Characteristics

Parameter	Description	Conditions	Min	Typ	Max	Units
T_A	Operating ambient temperature	–	–40	25.00	105	°C
T_J	Operating junction temperature	–	–40	–	125	°C
T_{JA}	Package θ_{JA} (56-pin QFN)	–	–	16.9	–	°C/watt
T_{JC}	Package θ_{JC} (56-pin QFN)	–	–	9.7	–	°C/watt
T_{JA}	Package θ_{JA} (76-ball WLCSP)	–	–	20.1	–	°C/watt
T_{JC}	Package θ_{JC} (76-ball WLCSP)	–	–	0.19	–	°C/watt
T_{JA}	Package θ_{JA} (76-ball Thin WLCSP)	–	–	20.9	–	°C/watt
T_{JC}	Package θ_{JC} (76-ball Thin WLCSP)	–	–	0.17	–	°C/watt

Table 57. Solder Reflow Peak Temperature

Package	Maximum Peak Temperature	Maximum Time at Peak Temperature
56-pin QFN	260 °C	30 seconds
76-ball WLCSP and Thin WLCSP	260 °C	30 seconds

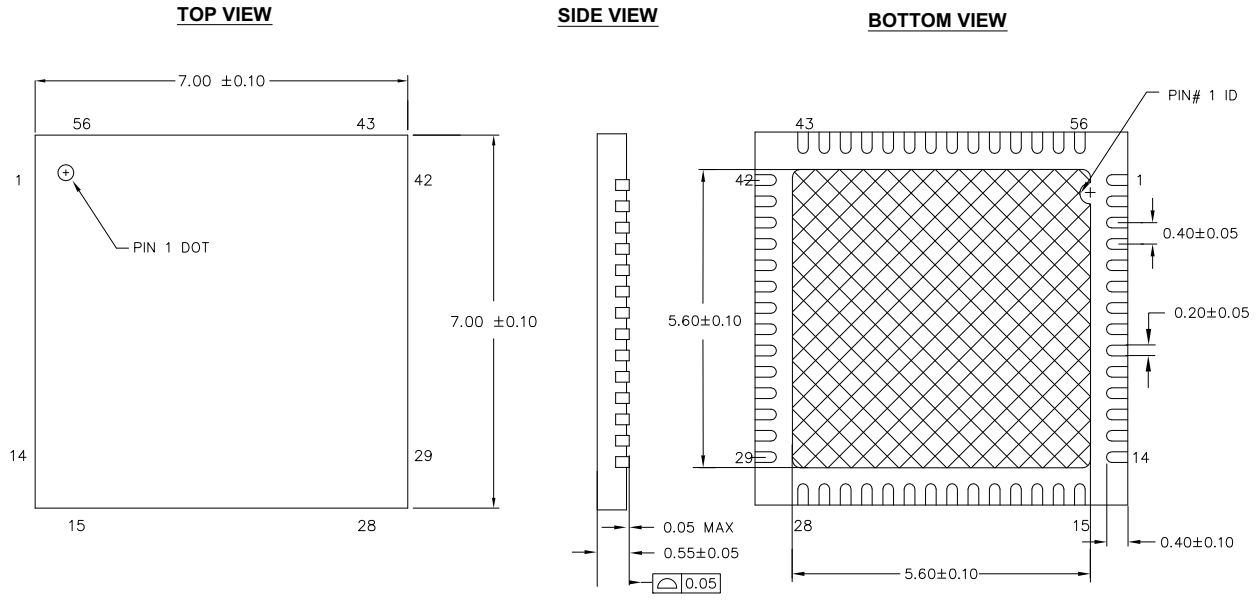
Table 58. Package Moisture Sensitivity Level (MSL), IPC/JEDEC J-STD-2

Package	MSL
56-pin QFN	MSL 3
76-ball WLCSP and Thin WLCSP	MSL 1

Table 59. Package Details

Spec ID	Package	Description
001-58740 Rev. *C	56-pin QFN	7.0 mm × 7.0 mm × 0.6 mm
001-96603 Rev. *A	76-ball WLCSP	4.04 mm × 3.87 mm × 0.55 mm
002-10658, Rev. **	76-ball thin WLCSP	4.04 mm × 3.87 mm × 0.4 mm

Figure 8. 56-Pin QFN 7 × 7 × 0.6 mm



NOTES:

1. HATCH AREA IS SOLDERABLE EXPOSED PAD
2. BASED ON REF JEDEC # MO-248
3. ALL DIMENSIONS ARE IN MILLIMETERS

001-58740 *C

The center pad on the QFN package should be connected to ground (VSS) for best mechanical, thermal, and electrical performance.

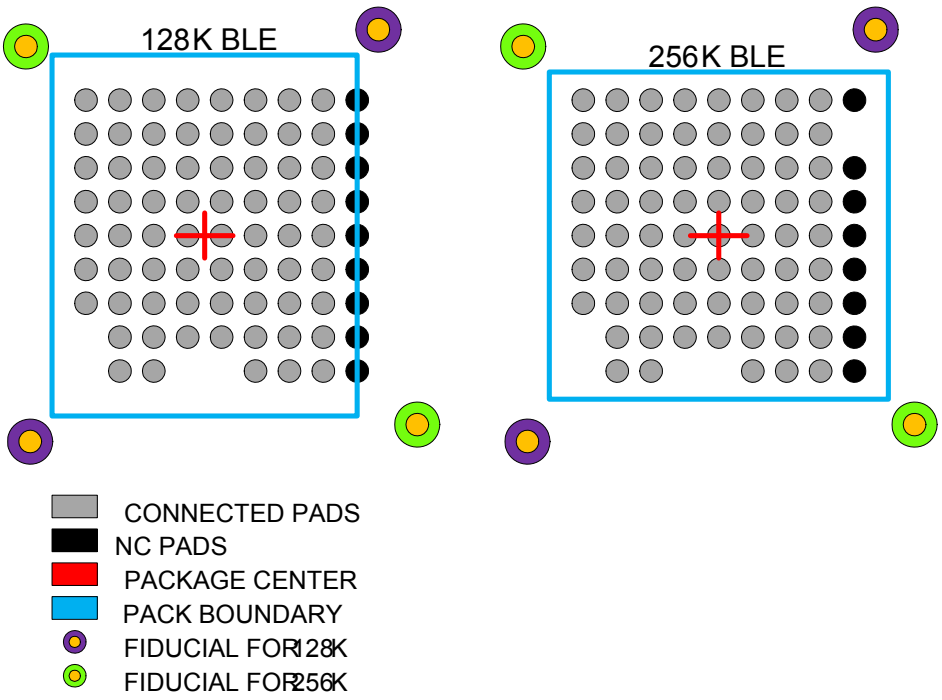
WLCSP Compatibility

The PSoC 4XXX_BLE family has products with 128 KB (16KB SRAM) and 256 KB (32KB SRAM) Flash. Package pin-outs and sizes are identical for the 56-pin QFN package but are different in one dimension for the 68-ball WLCSP.

The 256KB Flash product has an extra column of balls which are required for mechanical integrity purposes in the Chip-Scale package. With consideration for this difference, the land pattern on the PCB may be designed such that either product may be used with no change to the PCB design.

Figure 9 shows the 128KB and 256 KB Flash CSP packages.

Figure 9. 128KB and 256 KB Flash CSP Packages



The rightmost column of (all NC, No Connect) balls in the 256K BLE WLCSP is for mechanical integrity purposes. The package is thus wider (3.2 mm versus 2.8 mm). All other dimensions are identical. Cypress will provide layout symbols for PCB layout.

The scheme in Figure 9 is implemented to design the PCB for the 256K BLE package with the appropriate space requirements thus allowing use of either package at a later time without redesigning the Printed Circuit Board.

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